



DMN60H3D5SK3-13 Information

Heisener.com

Part Number DMN60H3D5SK3-13 **Manufacturer** Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET BVDSS: 501V 650V TO252 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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DMN60H3D5SK3-13 Specifications

Manufacturer Part Number DMN60H3D5SK3-13 Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Fermisitors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 2.8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 12.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 354pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds354pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs3.5 Ohm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 12.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
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Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) AlW (Tc) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	2.8A (Tc)
Gate Charge (Qg) (Max) @ Vgs 12.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 354pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	12.6nC @ 10V
FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	354pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±30V
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Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	41W (Tc)
Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	3.5 Ohm @ 1.5A, 10V
Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252, (D-Pak)
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

DMN60H3D5SK3-13 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

DMN60H3D5SK3-13 Payment Methods



















DMN60H3D5SK3-13 Shipping Methods













If you have any question about DMN60H3D5SK3-13, please do not hesitate to contact us!

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